MC14049B, MC14050B

Hex Buffer

The MC14049B Hex Inverter/Buffer and MC14050B Noninverting Hex Buffer are constructed with MOS P−Channel and N−Channel enhancement mode devices in a single monolithic structure. These complementary MOS devices find primary use where low power dissipation and/or high noise immunity is desired. These devices provide logic level conversion using only one supply voltage, V_{DD}.

The input−signal high level (V_{IH}) can exceed the V_{DD} supply voltage for logic level conversions. Two TTL/DTL loads can be driven when the devices are used as a CMOS−to−TTL/DTL converter (V_{DD} = 5.0 V, $V_{OL} \leq$ 0.4 V, $I_{OL} \geq$ 3.2 mA).

Note that pins 13 and 16 are not connected internally on these devices; consequently connections to these terminals will not affect circuit operation.

Features

- High Source and Sink Currents
- High−to−Low Level Converter
- Supply Voltage Range = 3.0 V to 18 V
- V_{IN} can exceed V_{DD}
- Meets JEDEC B Specifications
- Improved ESD Protection On All Inputs
- Pb−Free Packages are Available*

MAXIMUM RATINGS (Voltages Referenced to V_{SS})

Symbol	Parameter	Value	Unit
V_{DD}	DC Supply Voltage Range	−0.5 to +18.0	V
V_{in}	Input Voltage Range (DC or Transient)	−0.5 to +18.0	V
V_{out}	Output Voltage Range (DC or Transient)	−0.5 to V_{DD} + 0.5	V
I_{in}	Input Current (DC or Transient) per Pin	±10	mA
I_{out}	Output Current (DC or Transient) per Pin	±45	mA
P_D	Power Dissipation, per Package (Note 1) (Plastic) (SOIC)	 825 740	mW
T_A	Ambient Temperature Range	−55 to +125	°C
T_{stg}	Storage Temperature Range	−65 to +150	°C
T_L	Lead Temperature (8−Second Soldering)	260	°C

1. Temperature Derating: See Figure 3.

This device contains protection circuitry to protect the inputs against damage due to high static voltages or electric fields referenced to the V_{SS} pin only. Extra precautions must be taken to avoid applications of any voltage higher than the maximum rated voltages to this high−impedance circuit. For proper operation, the ranges $V_{SS} \leq V_{in} \leq 18$ V and $V_{SS} \leq V_{out} \leq V_{DD}$ are recommended.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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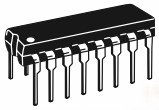
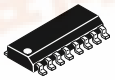
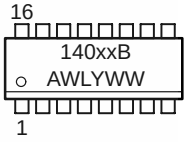
MARKING DIAGRAMS



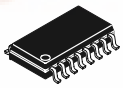
PDIP−16
P SUFFIX
CASE 648



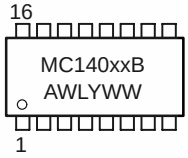
SOIC−16
D SUFFIX
CASE 751B



TSSOP−16
DT SUFFIX
CASE 948F



SOEIAJ−16
F SUFFIX
CASE 966

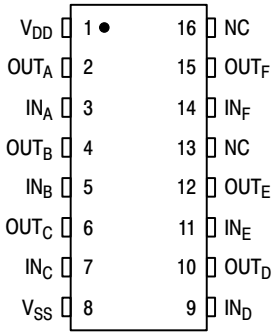


xx = Specific Device Code
A = Assembly Location
WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week

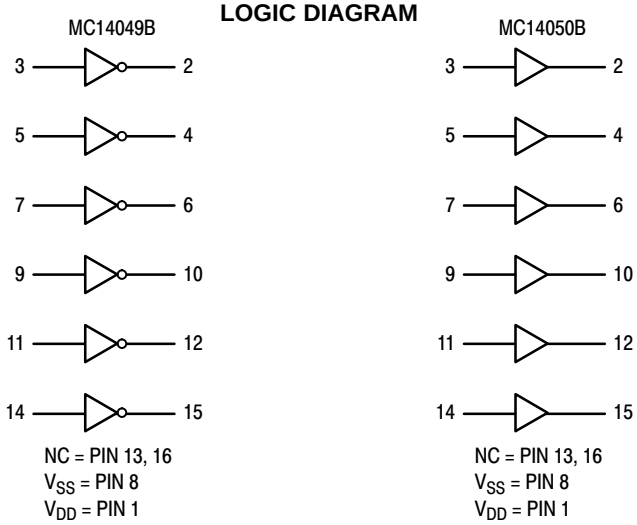
ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

PIN ASSIGNMENT



LOGIC DIAGRAM



ORDERING INFORMATION

Device	Package	Shipping†
MC14049BCP	PDIP−16	500 Units / Rail
MC14049BCPG	PDIP−16 (Pb−Free)	500 Units / Rail
MC14049BD	SOIC−16	48 Units / Rail
MC14049BDG	SOIC−16 (Pb−Free)	48 Units / Rail
MC14049BDR2	SOIC−16	2500 Units / Tape & Reel
MC14049BDR2G	SOIC−16 (Pb−Free)	2500 Units / Tape & Reel
MC14049BFEL	SOEIAJ−16	2000 Units / Tape & Reel
MC14050BCP	PDIP−16	500 Units / Rail
MC14050BCPG	PDIP−16 (Pb−Free)	500 Units / Rail
MC14050BD	SOIC−16	48 Units / Rail
MC14050BDR2	SOIC−16	2500 Units / Tape & Reel
MC14050BDR2G	SOIC−16 (Pb−Free)	2500 Units / Tape & Reel
MC14050BDT	TSSOP−16*	96 Units / Rail
MC14050BDTR2	TSSOP−16*	2500 Units / Tape & Reel
MC14050BFEL	SOEIAJ−16	2000 Units / Tape & Reel
MC14050BFELG	SOEIAJ−16 (Pb−Free)	2000 Units / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*This package is inherently Pb−Free.

ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

Characteristic		Symbol	V_{DD} Vdc	– 55°C Min	– 55°C Max	+ 25°C Min	+ 25°C Typ (Note 2)	+ 25°C Max	+ 125°C Min	+ 125°C Max	Unit
Output Voltage V_{in} = V_{DD}	"0" Level	V_{OL}	5.0 10 15	– – –	0.05 0.05 0.05	– – –	0 0 0	0.05 0.05 0.05	– – –	0.05 0.05 0.05	Vdc
 V_{in} = 0	"1" Level	V_{OH}	5.0 10 15	4.95 9.95 14.95	– – –	4.95 9.95 14.95	5.0 10 15	– – –	4.95 9.95 14.95	– – –	Vdc
Input Voltage (V_O = 4.5 Vdc) (V_O = 9.0 Vdc) (V_O = 13.5 Vdc)	"0" Level	V_{IL}	 5.0 10 15	 – – –	 1.5 3.0 4.0	 – – –	 2.25 4.50 6.75	 1.5 3.0 4.0	 – – –	 1.5 3.0 4.0	Vdc
 (V_O = 0.5 Vdc) (V_O = 1.0 Vdc) (V_O = 1.5 Vdc)	"1" Level	V_{IH}	 5.0 10 15	 3.5 7.0 11	 – – –	 3.5 7.0 11	 2.75 5.50 8.25	 – – –	 3.5 7.0 11	 – – –	Vdc
Output Drive Current (V_{OH} = 2.5 Vdc) (V_{OH} = 9.5 Vdc) (V_{OH} = 13.5 Vdc)	Source	I_{OH}	 5.0 10 15	 – 1.6 – 1.6 – 4.7	 – – –	 – 1.25 – 1.30 – 3.75	 – 2.5 – 2.6 – 10	 – – –	 – 1.0 – 1.0 – 3.0	 – – –	mAdc
(V_{OL} = 0.4 Vdc) (V_{OL} = 0.5 Vdc) (V_{OL} = 1.5 Vdc)	Sink	I_{OL}	5.0 10 15	3.75 10 30	– – –	3.2 8.0 24	6.0 16 40	– – –	2.6 6.6 19	– – –	mAdc
Input Current		I_{in}	15	–	± 0.1	–	±0.00001	± 0.1	–	± 1.0	μAdc
Input Capacitance (V_{in} = 0)		C_{in}	–	–	–	–	10	20	–	–	pF
Quiescent Current (Per Package)		I_{DD}	5.0 10 15	– – –	1.0 2.0 4.0	– – –	0.002 0.004 0.006	1.0 2.0 4.0	– – –	30 60 120	μAdc
Total Supply Current (Notes 3 & 4) (Dynamic plus Quiescent, per package) (C_L = 50 pF on all outputs, all buffers switching		I_T	5.0 10 15	I_T = (1.8 μA/kHz) f + I_{DD} I_T = (3.5 μA/kHz) f + I_{DD} I_T = (5.3 μA/kHz) f + I_{DD}							μAdc

2. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.
3. The formulas given are for the typical characteristics only at + 25°C
4. To calculate total supply current at loads other than 50 pF:

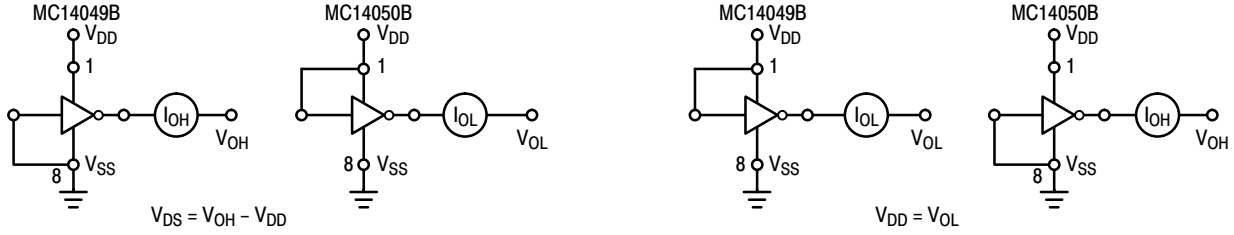
$$I_T(C_L) = I_T(50\ pF) + (C_L - 50)\ Vfk$$

Where: I_T is in μA (per Package), C_L in pF, V = (V_{DD} − V_{SS}) in volts, f in kHz is input frequency and k = 0.002.

AC SWITCHING CHARACTERISTICS (Note 5) (C_L = 50 pF, T_A = + 25°C)

Characteristic	Symbol	V_{DD} Vdc	Min	Typ (Note 6)	Max	Unit
Output Rise Time	t_{TLH}					ns
t_{TLH} = (0.7 ns/pF) C_L + 65 ns		5.0	–	100	160	
t_{TLH} = (0.25 ns/pF) C_L + 37.5 ns		10	–	50	80	
t_{TLH} = (0.2 ns/pF) C_L + 30 ns		15	–	40	60	
Output Fall Time	t_{THL}					ns
t_{THL} = (0.2 ns/pF) C_L + 30 ns		5.0	–	40	60	
t_{THL} = (0.06 ns/pF) C_L + 17 ns		10	–	20	40	
t_{THL} = (0.04 ns/pF) C_L + 13 ns		15	–	15	30	
Propagation Delay Time	t_{PLH}					ns
t_{PLH} = (0.33 ns/pF) C_L + 63.5 ns		5.0	–	80	140	
t_{PLH} = (0.19 ns/pF) C_L + 30.5 ns		10	–	40	80	
t_{PLH} = (0.06 ns/pF) C_L + 27 ns		15	–	30	60	
Propagation Delay Time	t_{PHL}					ns
t_{PHL} = (0.2 ns/pF) C_L + 30 ns		5.0	–	40	80	
t_{PHL} = (0.1 ns/pF) C_L + 15 ns		10	–	20	40	
t_{PHL} = (0.05 ns/pF) C_L + 12.5 ns		15	–	15	30	

5. The formulas given are for the typical characteristics only at 25°C.
6. Data labeled “Typ” is not to be used for design purposes but is intended as an indication of the IC’s potential performance.



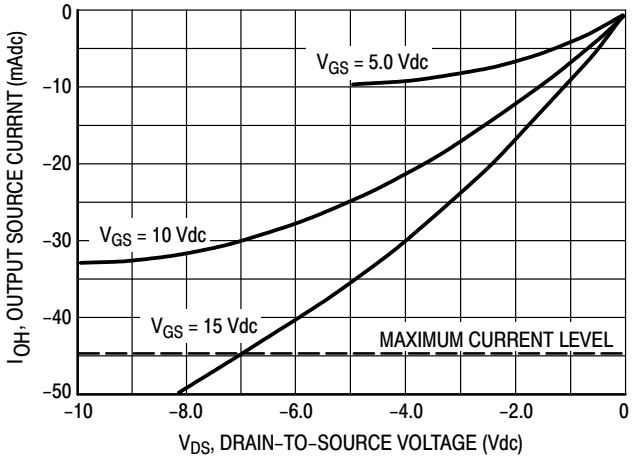


Figure 1. Typical Output Source Characteristics

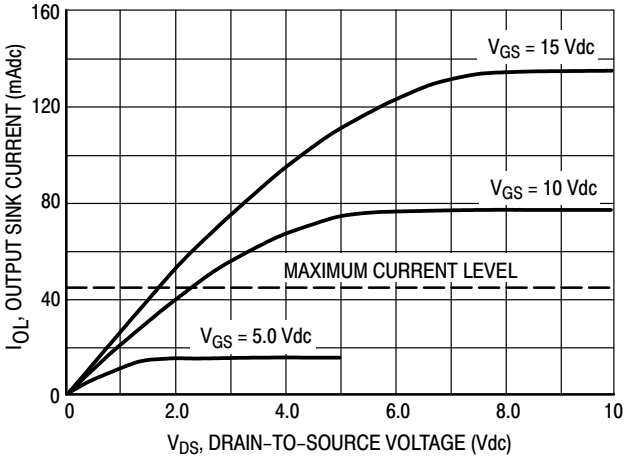


Figure 2. Typical Output Sink Characteristics

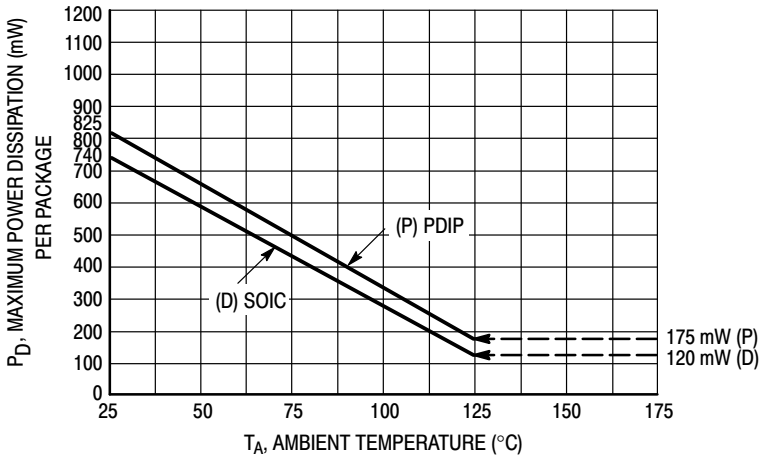


Figure 3. Ambient Temperature Power Derating

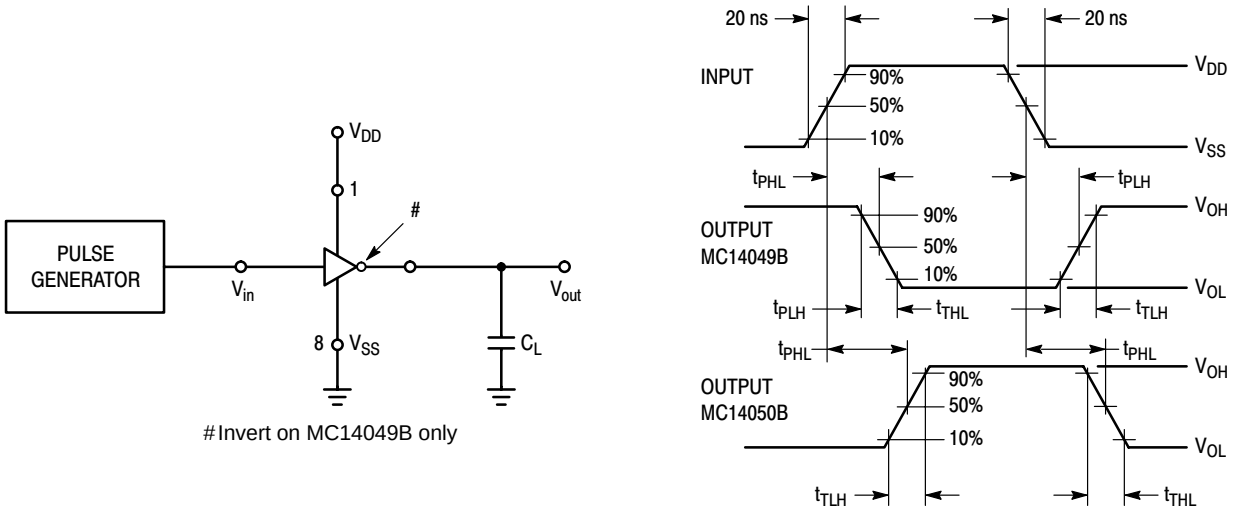
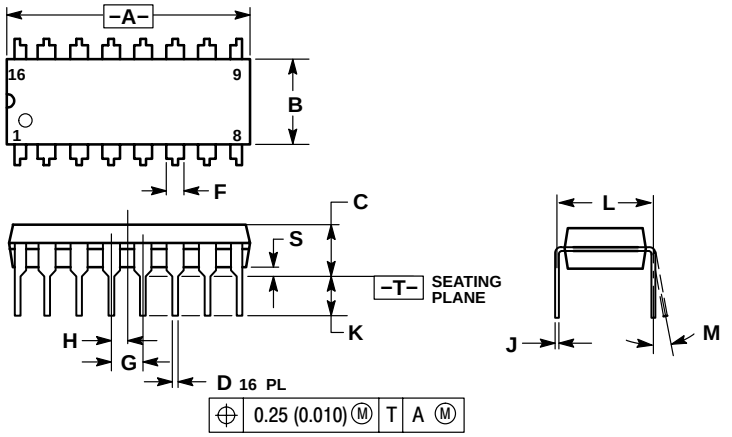


Figure 4. Switching Time Test Circuit and Waveforms

PACKAGE DIMENSIONS

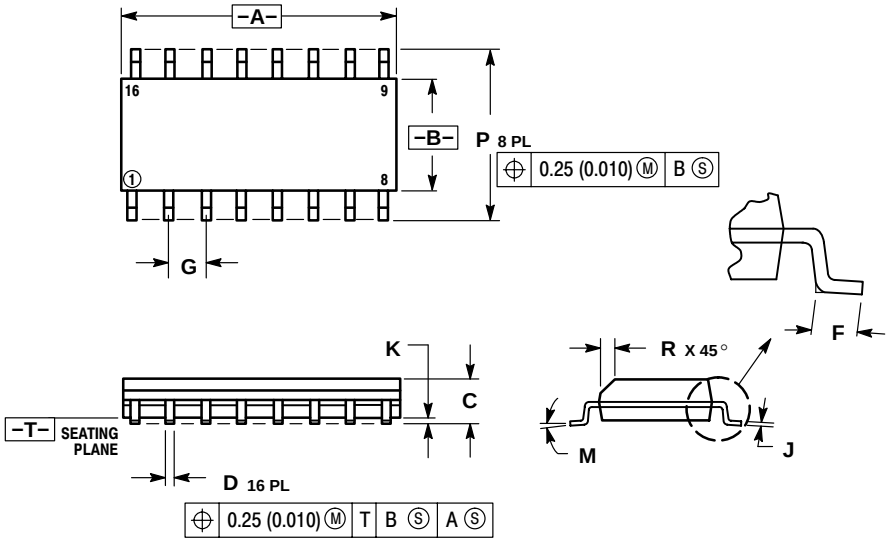
PDIP−16
P SUFFIX
PLASTIC DIP PACKAGE
CASE 648−08
ISSUE T



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
5. ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.740	0.770	18.80	19.55
B	0.250	0.270	6.35	6.85
C	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.70	1.02	1.77
G	0.100 BSC		2.54 BSC	
H	0.050 BSC		1.27 BSC	
J	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
M	0 °	10 °	0 °	10 °
S	0.020	0.040	0.51	1.01

SOIC−16
D SUFFIX
PLASTIC SOIC PACKAGE
CASE 751B−05
ISSUE J

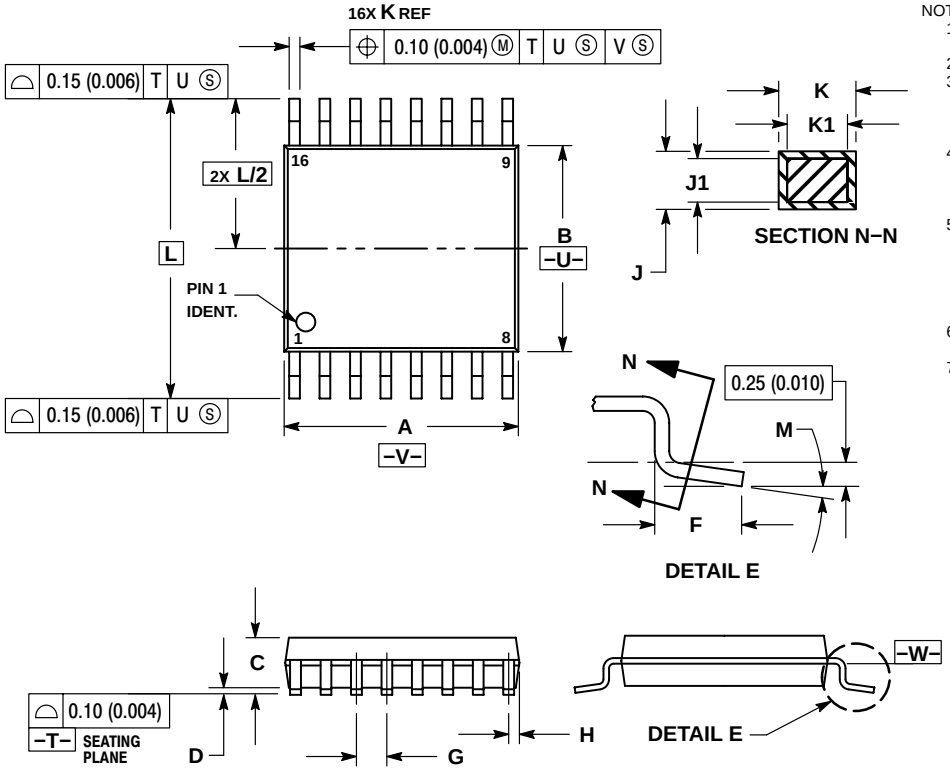


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	9.80	10.00	0.386	0.393
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0 °	7 °	0 °	7 °
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

PACKAGE DIMENSIONS

TSSOP−16
DT SUFFIX
PLASTIC TSSOP PACKAGE
CASE 948F−01
ISSUE A

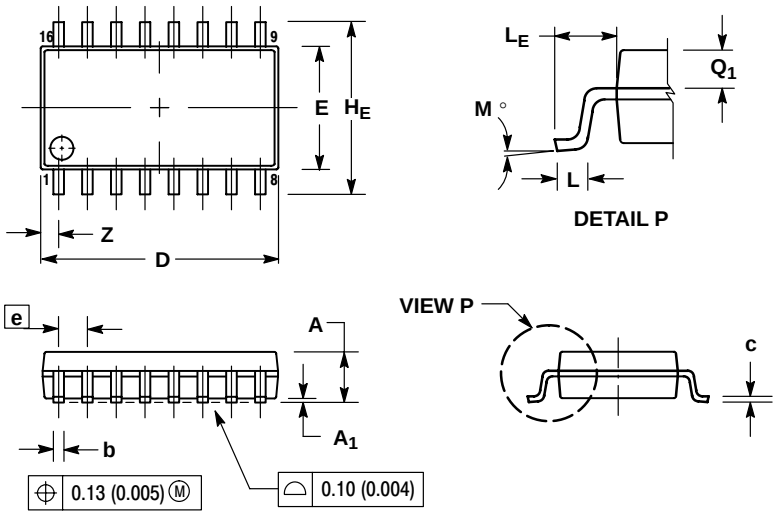


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE −W−.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	−−−	1.20	−−−	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0 °	8 °	0 °	8 °

PACKAGE DIMENSIONS

SOEIAJ−16
F SUFFIX
PLASTIC EIAJ SOIC PACKAGE
CASE 966−01
ISSUE O



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	---	2.05	---	0.081
A_1	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
c	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
e	1.27 BSC		0.050 BSC	
H_E	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
L_E	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10 °
Q_1	0.70	0.90	0.028	0.035
Z	---	0.78	---	0.031

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
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